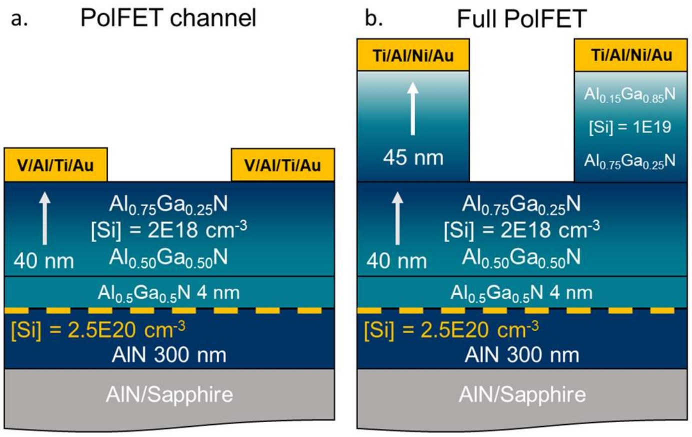

Figure 1. Epitaxial layer diagrams for the devices discussed in this abstract.

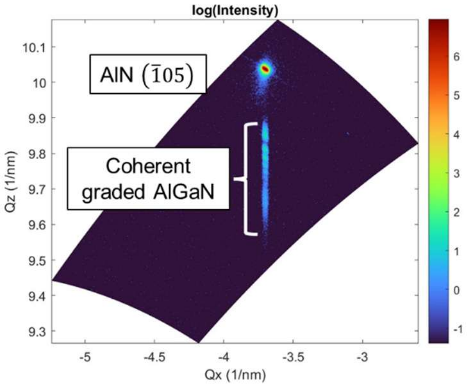

Figure 2. RSM of the full PolFET structure showing the AlGaN is coherently strained to the substrate.

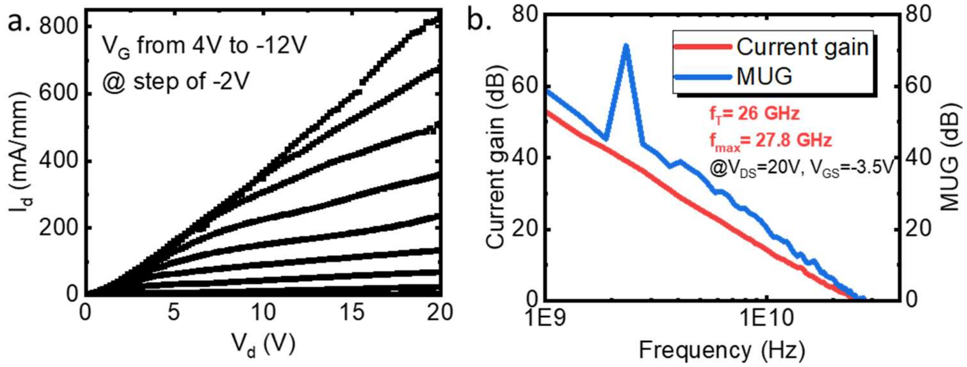

Figure 3. a) Drain current vs voltage and current gain and b) unilateral power gain vs frequency for the highly scaled channel-only PolFET.

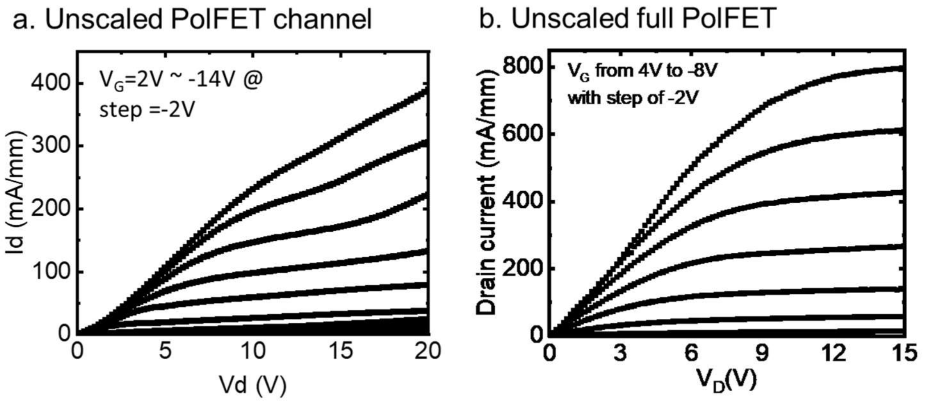

Figure 4. Drain current vs voltage plots for a) the unscaled channel-only PolFET and b) the unscaled PolFET with reverse-graded contacts showing a factor of 2 improvement in maximum drain current.